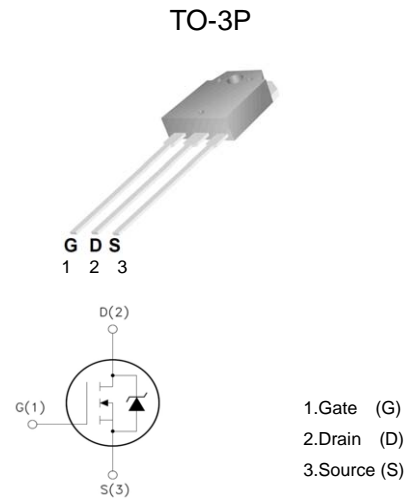


Features

- Low Intrinsic Capacitances.
- Excellent Switching Characteristics.
- Extended Safe Operating Area.
- Unrivalled Gate Charge: Qg= 77nC (Typ.).
- BVDSS=300V, I_D=59A
- R_{DS(on)} : 0.056Ω (Max) @V_G=10V
- 100% Avalanche Tested

Package



Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	300	V
I _D	Drain Current	T _C =25°C	59
		T _C =100°C	35
V _{GS(TH)}	Gate Threshold Voltage	±30	V
E _{AS}	Single Pulse Avalanche Energy (note1)	1734	mJ
I _{AR}	Avalanche Current (note2)	59	A
P _D	Power Dissipation (T _j =25°C)	500	W
T _j	Junction Temperature(MAX)	150	°C
T _{stg}	Storage Temperature	-55~+150	°C
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance, Junction to Case	-	0.25	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	-	40	°C/W



Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0	300	-	-	V
Δ BVDSS/ Δ T _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, Reference to 25°C	-	0.3	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =300V, V _{GS} =0V	-	-	10	μA
		V _{DS} =240V, T _C =125°C	-	-	100	
I _{GSSF}	Gate-body leakage Current, Forward	V _{GS} =+30V, V _{DS} =0V	-	-	100	nA
I _{GSSR}	Gate-body leakage Current, Reverse	V _{GS} =-30V, V _{DS} =0V	-	-	-100	
On Characteristics						
V _{GS(TH)}	Gate Threshold Voltage	I _D =250μA, V _{DS} =V _{GS}	3	-	5	V
R _{DS(ON)}	Static Drain-Source On-Resistance	I _D =29.5A, V _{GS} =10V	-	0.047	0.056	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0, f=1.0MHz	-	3590	-	pF
C _{oss}	Output Capacitance		-	710	-	
C _{rss}	Reverse Transfer Capacitance		-	80	-	
Switching Characteristics						
T _{d(on)}	Turn-On Delay Time	V _{DD} =150V, I _D =59A, R _G =25Ω (Note 4,5)	-	140	290	ns
T _r	Turn-On Rise Time		-	575	1160	
T _{d(off)}	Turn-Off Delay Time		-	120	250	
T _f	Turn-Off Rise Time		-	200	410	
Q _g	Total Gate Charge	V _{DS} =240V, V _{GS} =10V, I _D =59A (Note 4,5)	-	77	100	nC
Q _{gs}	Gate-Source Charge		-	22	-	
Q _{gd}	Gate-Drain Charge		-	40	-	
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Max. Diode Forward Current	-	-	-	59	A
I _{SM}	Max. Pulsed Forward Current	-	-	-	236	
V _{SD}	Diode Forward Voltage	I _D =59A	-	-	1.4	V
T _{rr}	Reverse Recovery Time	I _S =59A, V _{GS} =0V, diF/dt=100A/μs (Note4)	-	246	-	nS
Q _{rr}	Reverse Recovery Charge	(Note4)	-	6.9	-	μC

Notes : 1, L=0.83mH, I_{AS}= A, V_{DD}=50V, R_G=25Ω, Starting T_J =25°C
 2, Repetitive Rating : Pulse width limited by maximum junction temperature
 3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
 4, Essentially Independent of Operating Temperature

Typical Characteristics

Figure 1. On-Region Characteristics

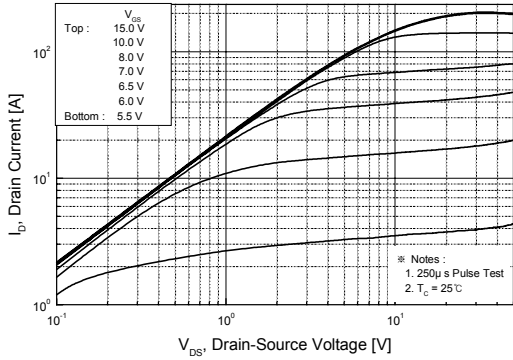


Figure 2. Transfer Characteristics

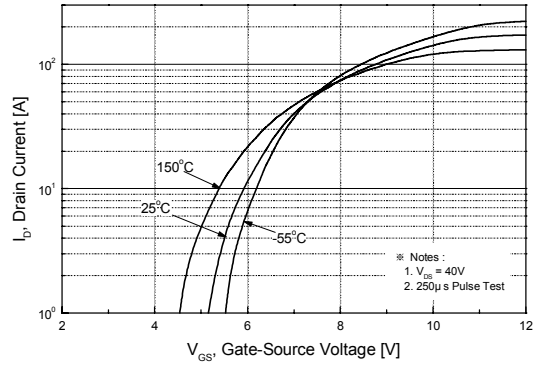


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

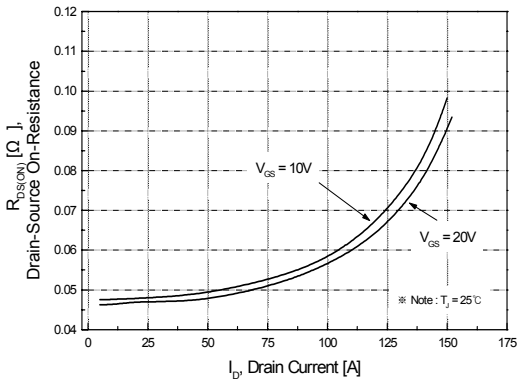


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

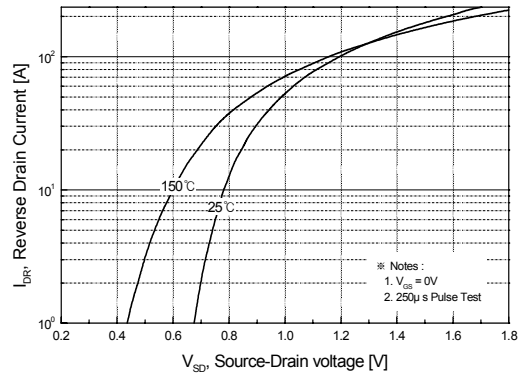


Figure 5. Capacitance Characteristics

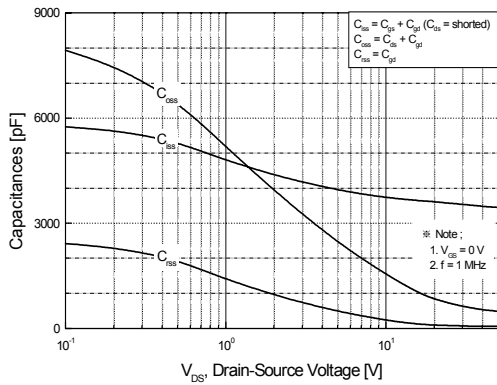
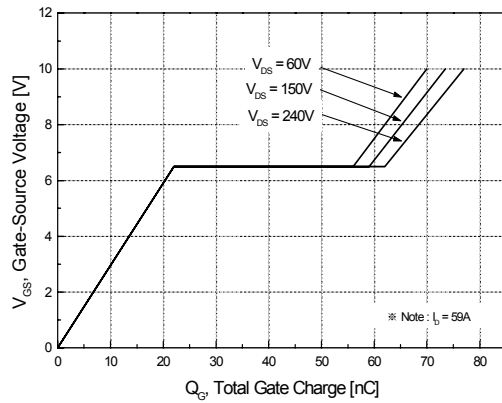


Figure 6. Gate Charge Characteristics



Typical Characteristics

Figure 7. Breakdown Voltage Variation vs. Temperature

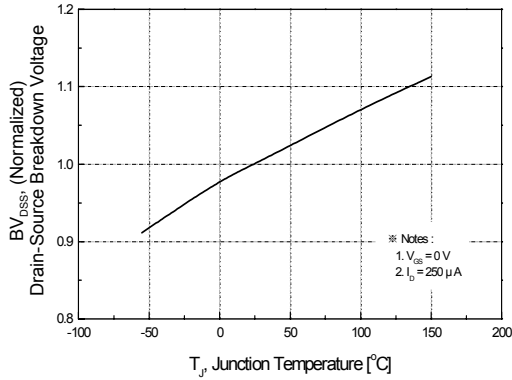


Figure 8. On-Resistance Variation vs. Temperature

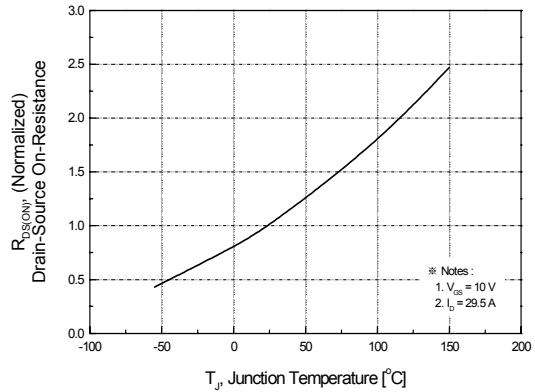


Figure 9. Maximum Safe Operating Area

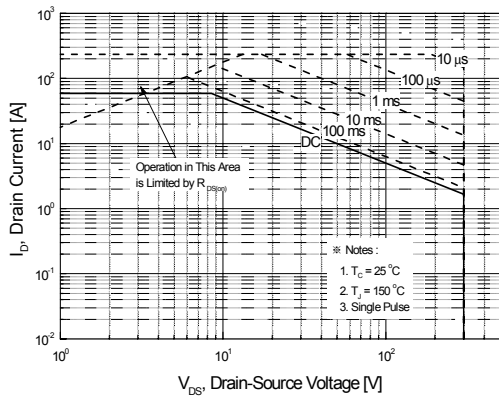
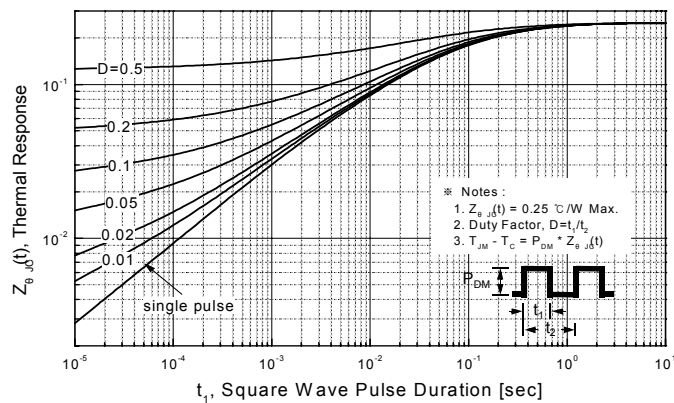
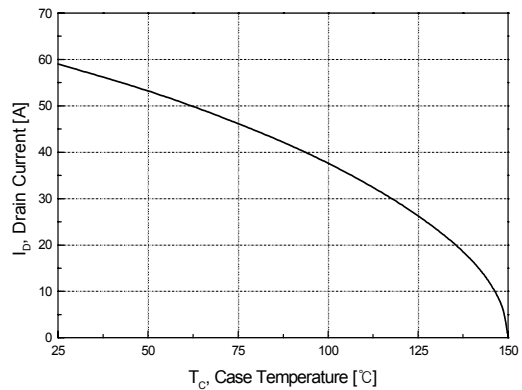
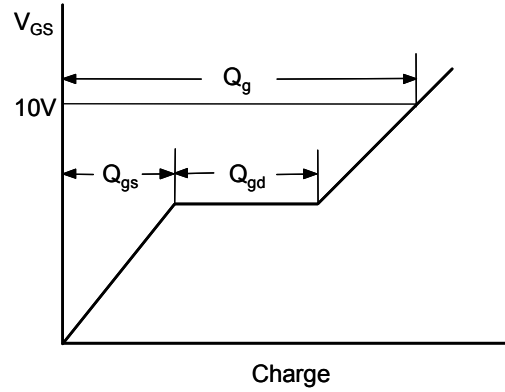
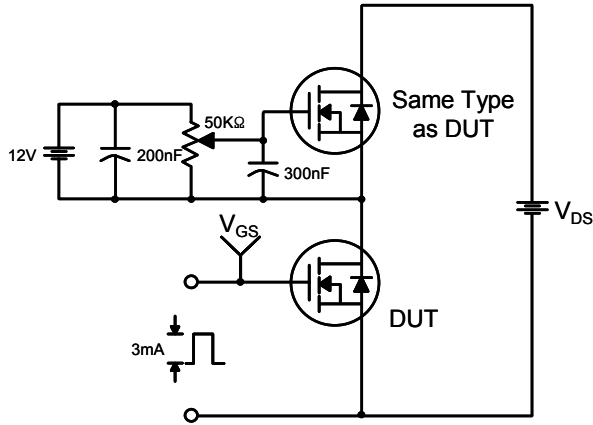


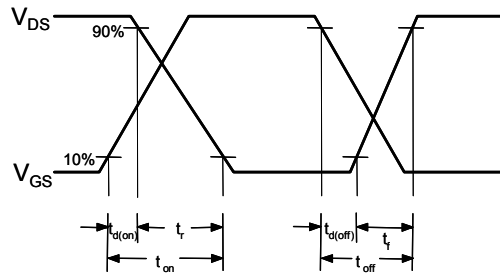
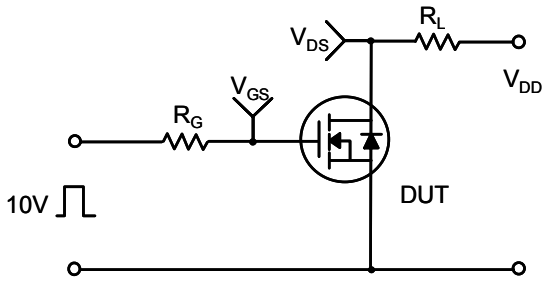
Figure 10. Maximum Drain Current vs. Case Temperature



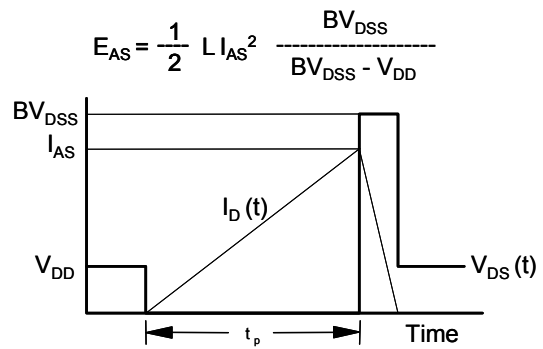
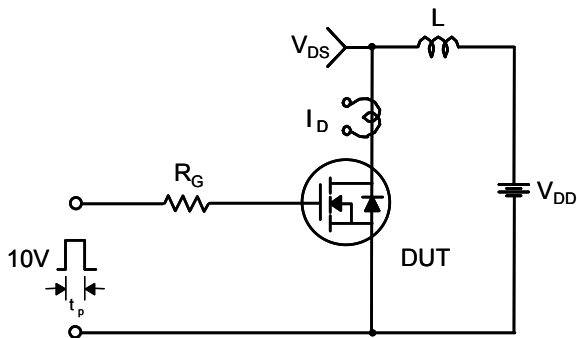
Gate Charge Test Circuit & Waveform



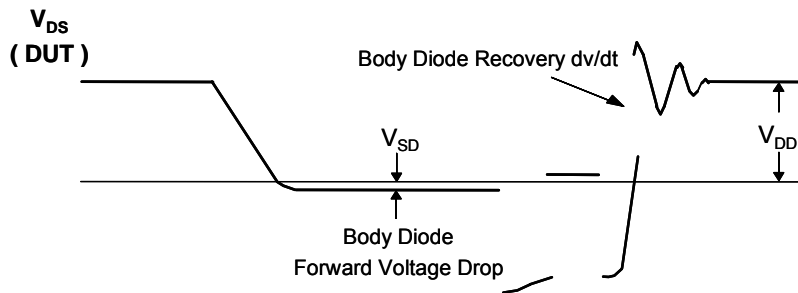
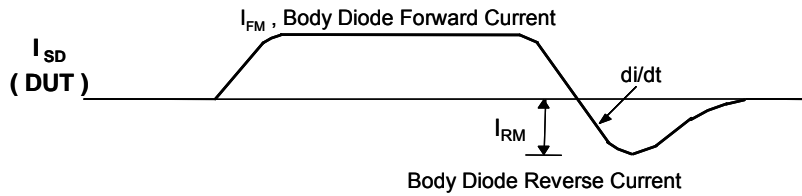
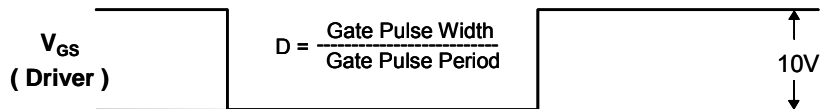
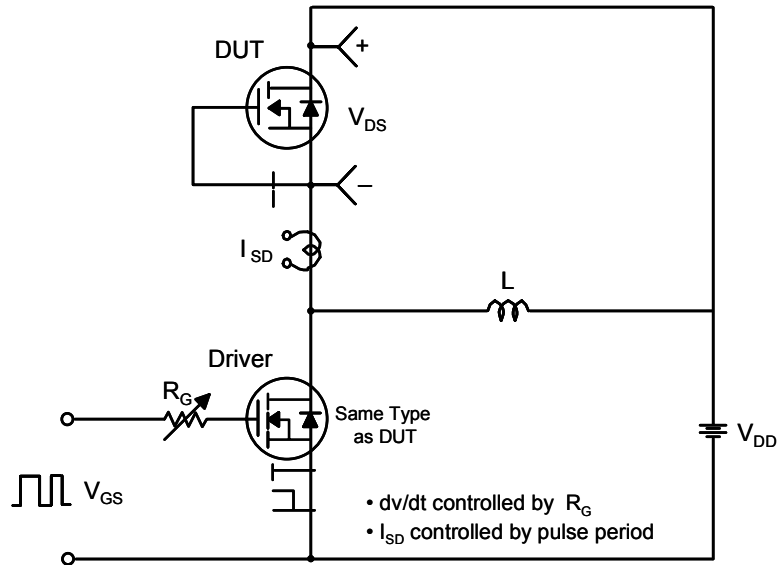
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



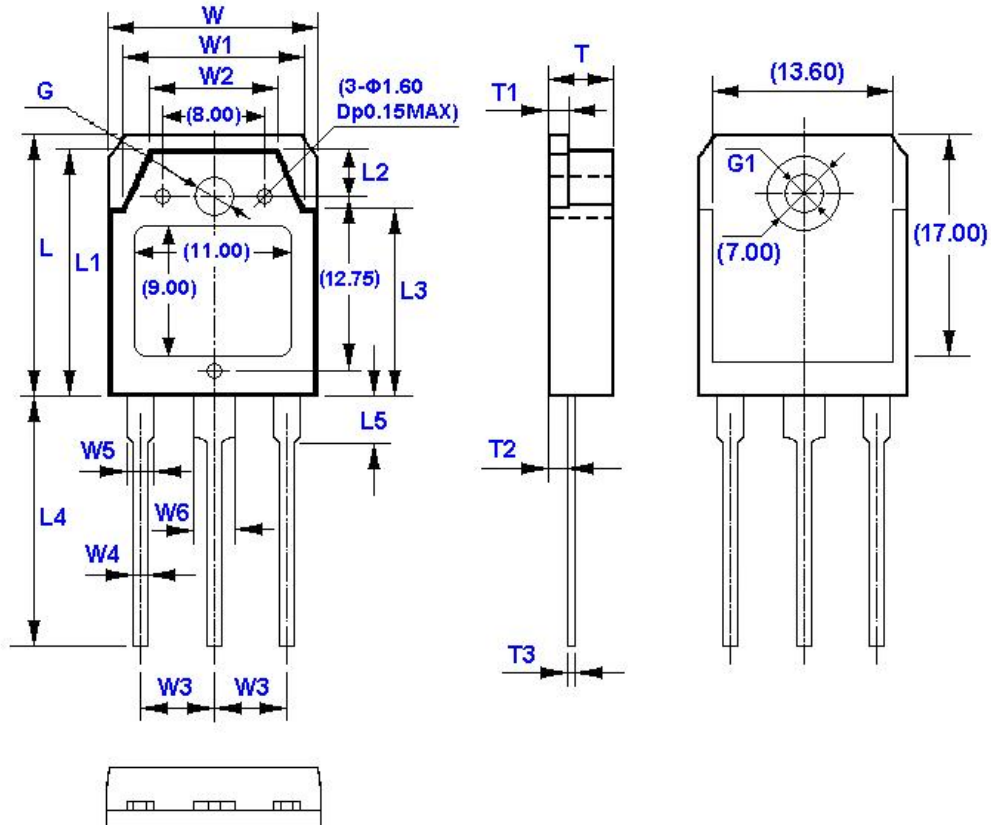
Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

TO-3P

Unit: mm



Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	15.40	15.80	W5	1.80	2.20	L3	13.70	14.10	T2	1.20	1.60
W1	13.40	13.80	W6	2.80	3.20	L4	19.70	20.30	T3	0.55	0.75
W2	9.40	9.80	L	19.70	20.10	L5	3.30	3.70	G (Φ) (Front)	3.30	3.50
W3	5.45 (TYP)		L1	18.50	18.90	T	4.60	5.00	G1(Φ) (Back)	3.10	3.30
W4	0.80	1.20	L2	3.60	4.00	T1	1.45	1.65			